# **SQ4470EY**

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**Vishay Siliconix** 

# Automotive N-Channel 60 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V <sub>DS</sub> (V)	60			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 V$	0.012			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 6 V$	0.014			
I <sub>D</sub> (A)	16			
Configuration	Single			

#### **FEATURES**

- TrenchFET<sup>®</sup> power MOSFET
- AEC-Q101 qualified<sup>c</sup>
- 100 %  $R_{\rm q}$  and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

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ROHS COMPLIANT HALOGEN FREE

Configuration	Single	N-Channel MOSFET		
ORDERING INFORMA	ΓΙΟΝ			
Package		SO-8		
Lead (Pb)-free and halogen-free	9	SQ4470EY (for detailed order number please see www.vishav.com/doc?7977		

<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_c = 25 \degree C$ , unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		V <sub>DS</sub>	60	v	
Gate-source voltage		V <sub>GS</sub>	± 20		
Continuous drain current	T <sub>C</sub> = 25 °C		16		
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	9		
Continuous source current (diode conduction)		۱ <sub>S</sub>	6	A	
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	67		
Single pulse avalanche current		I <sub>AS</sub>	50		
Single pulse avalanche energy	L = 0.1 mH	E <sub>AS</sub>	125	mJ	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	P	7.1	- w	
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	2.3		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-ambient	PCB mount <sup>b</sup>	R <sub>thJA</sub>	80	°C/W	
Junction-to-case (drain)	on-to-case (drain)		21	C/W	

#### Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

b. When mounted on 1" square PCB (FR-4 material)

c. Parametric verification ongoing

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static				I	<u> </u>	<u> </u>	
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0, I_D = 250 \ \mu A$		60	-	-	v
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		3.0	3.5	
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V	-	-	1.0	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 125 °C	-	-	50	μA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 60 V, T <sub>J</sub> = 175 °C	-	-	250	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 V$	30	-	-	Α
		$V_{GS} = 10 V$	I <sub>D</sub> = 6 A	-	0.010	0.012	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A, T <sub>J</sub> = 125 °C	-	-	0.021	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 6 A, T <sub>J</sub> = 175 °C	-	-	0.025	
		$V_{GS} = 6 V$	I <sub>D</sub> = 5 A	-	0.012	0.014	
Forward transconductance b	g <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 6 A	-	25	-	S
Dynamic <sup>b</sup>	•	·					
Input capacitance	C <sub>iss</sub>			-	2531	3165	pF
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	382	480	
Reverse transfer capacitance	C <sub>rss</sub>	1		-	153	195	
Total gate charge <sup>c</sup>	Qg			-	45	68	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 30 \text{ V}, I_{D} = 12 \text{ A}$	-	9.9	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>	1		-	11.2	-	
Gate resistance	R <sub>g</sub>	f = 1 MHz		0.40	0.87	1.30	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>	$\label{eq:V_DD} \begin{array}{l} V_{DD}=30 \text{ V}, \text{ R}_L=2.5 \ \Omega \\ \text{I}_D\cong 12 \text{ A}, \text{ V}_{GEN}=10 \text{ V}, \text{ R}_g=1 \ \Omega \end{array}$		-	13	20	
Rise time <sup>c</sup>	tr			-	12	18	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	25	38	ns
Fall time <sup>c</sup>	t <sub>f</sub>			-	9	14	
Source-Drain Diode Ratings and Char	racteristics <sup>b</sup>	·					
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	67	А
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = 1.7 A, V <sub>GS</sub> = 0		-	0.72	1.2	V

Notes

d. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

e. Guaranteed by design, not subject to production testing

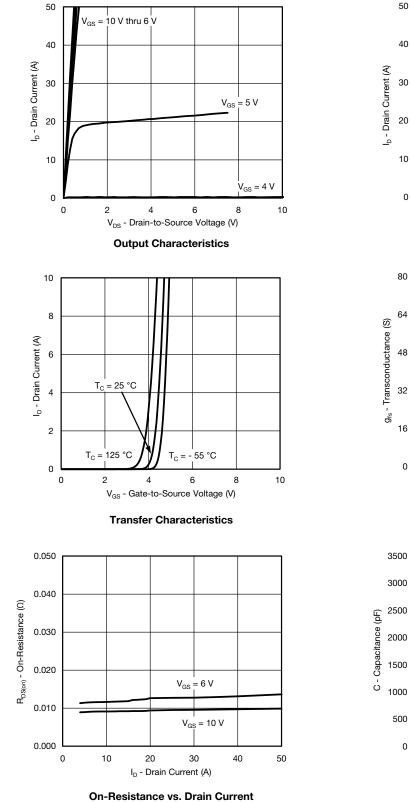
f. Independent of operating temperature

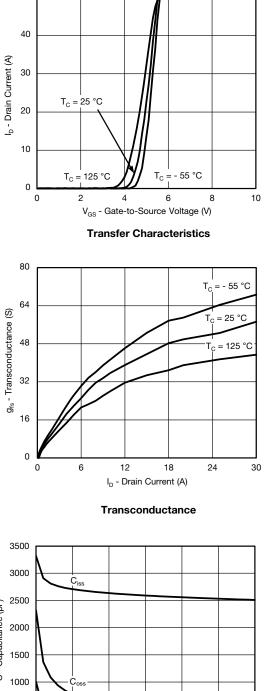
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)





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V<sub>DS</sub> - Drain-to-Source Voltage (V)

20

25

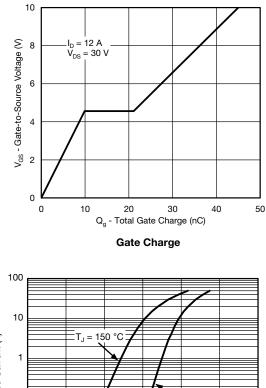
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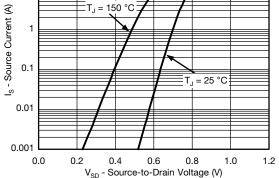
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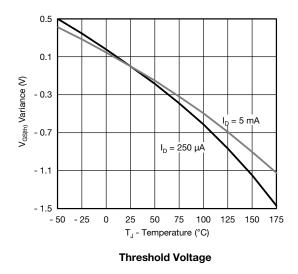


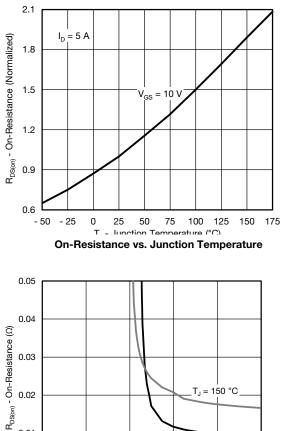
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

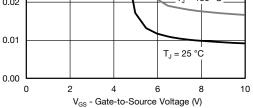




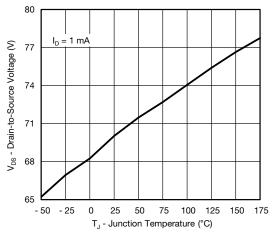
Source Drain Diode Forward Voltage







**On-Resistance vs. Gate-to-Source Voltage** 



Drain Source Breakdown vs. Junction Temperature

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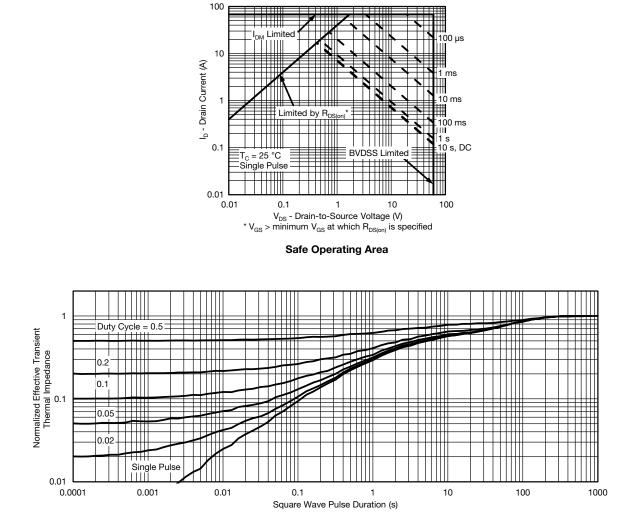
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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

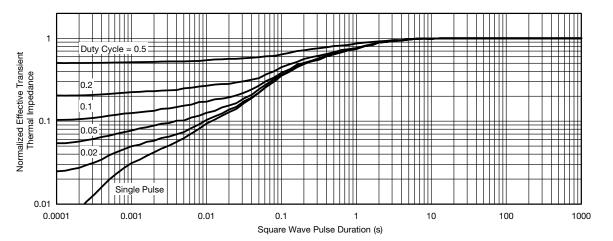


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#### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

The characteristics shown in the two graphs

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- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65673.



# Package Information

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# SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012

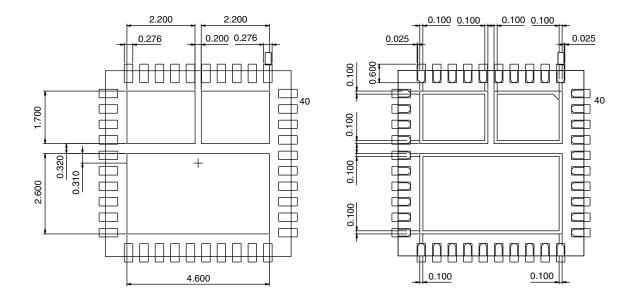




	MILLIM	IETERS	INCHES		
DIM	Min	Мах	Min	Max	
A	1.35	1.75	0.053	0.069	
A <sub>1</sub>	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	
S	0.44	0.64	0.018	0.026	
ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498					



# **Recommended Land Pattern PowerPAK® MLP66-40L**



All Dimensions are in milimeters

# **Application Note 826**

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**RECOMMENDED MINIMUM PADS FOR SO-8** 



Recommended Minimum Pads Dimensions in Inches/(mm)

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